



SHENZHEN LONG JING MICRO-ELECTRONICS CO., LTD.

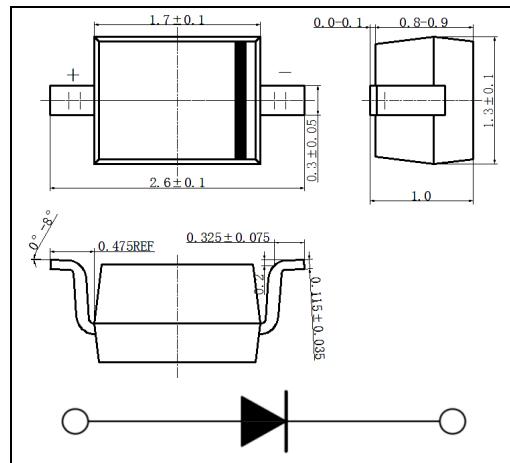
SOD-323 Plastic-Encapsulate Diodes

1N4148WS

Fast Switching Diode

Features

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance

Marking: T4**Maximum Ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)**

Symbol	Parameter	Value	Unit
V_{RM}	Non-Repetitive Peak Reverse Voltage	100	V
V_{RRM}	Peak Repetitive Peak Reverse Voltage		V
V_{RWM}	Working peak reverse voltage	100	V
V_R	DC blocking voltage		V
$V_{R(RMS)}$	RMS reverse voltage	71	V
I_{FM}	Forward Continuous Current	300	mA
I_o	Average Rectified Output Current	150	mA
I_{FSM}	Non-Repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	2.0	A
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	625	°C/W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

Electrical Characteristics ($T_a=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{F1}	Forward voltage	$I_F = 1\text{mA}$			0.715	V
V_{F2}		$I_F = 10\text{mA}$			0.855	V
V_{F3}		$I_F = 50\text{mA}$			1.0	V
V_{F4}		$I_F = 150\text{mA}$			1.25	V
I_{R1}	Reverse current	$V_R = 75\text{V}$			1	μA
I_{R2}		$V_R = 20\text{V}$			25	nA
C_T	Capacitance between terminals	$V_R = 0\text{V}, f = 1\text{MHz}$			2	pF
t_{rr}	Reverse recovery time	$I_F = I_R = 10\text{mA}$ $I_{rr} = 0.1 \times I_R, R_L = 100\Omega$			4	ns

Typical Characteristics

